

**VOLTAGE RANGE: 100V**

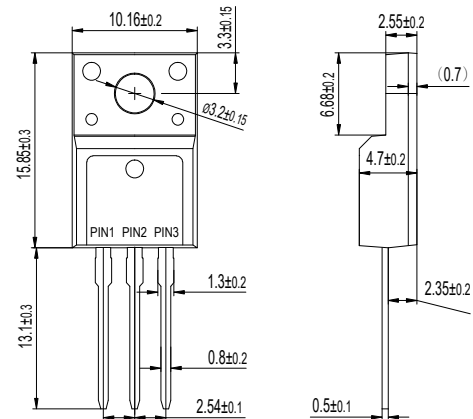
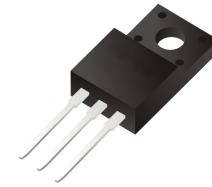
**CURRENT: 10A**

### Features

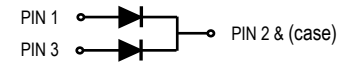
- Ultra low  $v_f$
- High efficiency operation
- Low power loss
- Low stored charge majority carrier conduction
- High forward surge capability
- Lead free in compliance with EU RoHS 2011/65/EU directive

### Mechanical Data

- Circuit figure: Common cathode
- Leads: Solderable per mil-std-202, Method 208
- Polarity: as marked
- Mounting torque: 5 in-lbs maximum
- Terminals: Puretin plated
- Weight: ITO-220AB 1.70 grams



ITO-220AB



### Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise specified

RATINGS	SYMBOL	MBRF10L100CT	UNIT
Maximum repetitive reverse voltage	VRRM	100	V
Maximum RMS voltage	VRMS	70	V
Maximum DC blocking voltage	VDC	100	V
Maximum average forward current per device per diode	IAV	10 5	A
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load	IFSM	150	A
Typical thermal resistance per diode (Note 1)	R $\theta$ -JC	4.5	$^\circ\text{C}/\text{W}$
Operating junction temperature range	TJ	-55 to +150	$^\circ\text{C}$
Storage temperature range	TSTG	-55 to +150	$^\circ\text{C}$

## Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Breakdown voltage per diode	V <sub>BR</sub>	I <sub>R</sub> =0.5mA	100	-	-	V
Instantaneous forward voltage per diode	V <sub>F</sub>	I <sub>F</sub> =5A      T <sub>J</sub> =25°C	-	0.67	0.70	V
		I <sub>F</sub> =5A      T <sub>J</sub> =125°C	-	-	0.62	V
Reverse current per diode	I <sub>R</sub>	V <sub>R</sub> =100V      T <sub>J</sub> =25°C	-	-	100	μA
		T <sub>J</sub> =125°C	-	-	30	mA

